LIST OF PUBLICATIONS

In International Journals:

1. The influence of temperature fluctuations on melt growth of antimony sulfoiodide.
   L. Palaniappan, F.D. Gnanam and P. Ramasamy

2. Growth habits of SbSeI and microhardness studies.
   L. Palaniappan, S. Anbukumar, F.D. Gnanam and P. Ramasamy

3. Electrical characterisation of SbSI grown from the melt by temperature fluctuation technique.
   L. Palaniappan, P.D. Gnanam and P. Ramasamy

4. Microhardness study of ingots of SbSI and SbSeI crystals.
   L. Palaniappan, S. Anbukumar, F.D. Gnanam and P. Ramasamy

5. Growth and electrical characterisation of SbSI and SbSOI crystals.
   L. Palaniappan, M. Shanmugam, F.D. Gnanam and P. Ramasamy

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7. Electrical characterisation of SbSeI grown from melt by vertical Bridgman technique.
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8. Growth of SbSeI crystals by vertical Bridgman technique.
   V.N. Meni, L. Palaniappan, F.D. Gnanam and P. Ramasamy
   Indian Journal of Physics (in print).
9. Electrical conductivity study of SbSI ingot at low temperature.

L. Palaniappan, P.D. Gnanam and P. Ramasamy
Semiconductor Science and Technology (communicated).

10. Microhardness study of SbSI single crystals

L. Palaniappan, P.D. Gnanam and P. Ramasamy

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L. Palaniappan, D. Arivuoli, P.D. Gnanam and P. Ramasamy
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Bangalore, India, April 17-19, 1984.

13. Growth of SbSeI from melt.

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15. Growth of SbSeI by Bridgman method.

L. Palaniappan, K.A. Ravindran and P. Ramasamy


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17. Growth of mixed crystals of antimony tri-iodide and arsenic tri-iodide from vapour.

D. Arivuoli, L. Palaniappan, F.D. Gnanam and P. Ramasamy
IV National Seminar on Physics of Semiconductors and Devices, Department of Physics, University of Rajasthan, Jaipur-302 004, India, January 16-18, 1985.

18. Growth of BiSI single crystals and study of its growth Habits.

L. Palaniappan, V.N. Mani, F.D. Gnanam and P. Ramasamy
V National Seminar on Physics of Semiconductors and Devices, Department of Physics and Department of Electronics Engineering, Banaras Hindu University, Varanasi-221 005, India, December 5-7, 1985.


L. Palaniappan, M. Shanmugam, F.D. Gnanam and P. Ramasamy

20. Growth of SbSeI crystals by vertical Bridgman technique.

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21. Growth and electrical characterisation of SbSI and SbSbO crystals.

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22. Microhardness study of SbSI single crystals.

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III National Seminar on Crystal Growth, Crystal Growth Centre, Anna University, Madras 600 025, India, February 16-19, 1987.